SP010N07AGTQ

100V N-Channel Power MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	6.7mΩ@10V	90A
	8.7mΩ@4.5V	

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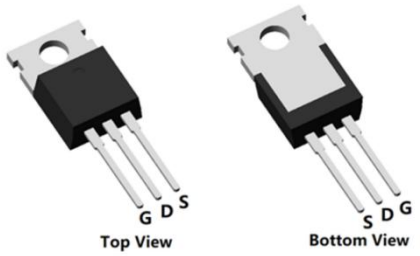
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

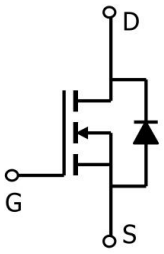
- Power switching application
- Battery management
- Uninterruptible power supply

Package

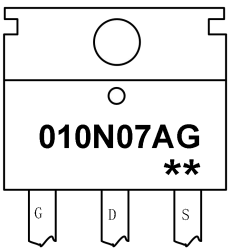


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



010N07AG : Product code
**** : Week code**

Order Information

Device	Package	Unit/Tube
SP010N07AGTQ	TO-220-3L	50

Absolute maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (Tc=25℃)	I_D	90	A
Continuous Drain Current (Tc=100℃)	I_D	60	A
Pulsed Drain Current	I_{DM}	360	A
Single Pulse Avalanche Energy[1]	E_{AS}	272	mJ
Power Dissipation (Tc=25℃)	P_D	130	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.96	℃/W
Storage Temperature Range	T_{STG}	55 to 150	℃
Operating Junction Temperature Range	T_J	55 to 150	℃

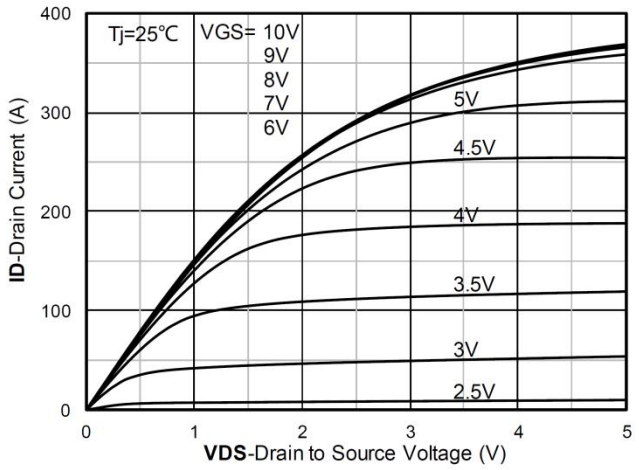
Electrical characteristics (Ta=25℃, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	100	-	-	V
Drain Cut-Off Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V	-	-	1	uA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.7	2.5	V
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 30A	-	6.7	8.5	mΩ
		V_{GS} = 4.5V, I_D = 25A	-	8.7	12	
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} =50V, V_{GS} = 0V, f = 1.0MHz	-	1942	-	pF
Output Capacitance	C_{oss}		-	388	-	
Reverse Transfer Capacitance	C_{rss}		-	12	-	
Total Gate Charge	Q_g	V_{DS}=50V , VGS=10V , ID=50A	-	67	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	
Gate-Drain Charge	Q_{gd}		-	21	-	
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 50V, V_{DS} =50V, ID=50A R_G = 4.7Ω	-	12	-	nS
Rise Time	t_r		-	11	-	
Turn-Off Delay Time	$t_{d(off)}$		-	42	-	
Fall Time	t_f		-	6	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	V_{GS}=0V , I_S=1A , T_J=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I_S		-	-	90	A
Reverse Recovery Time	Trr	I_S=20A, di/dt=100A/us, T_J=25℃	-	59	-	nS
Reverse Recovery Charge	Qrr		-	88	-	nC

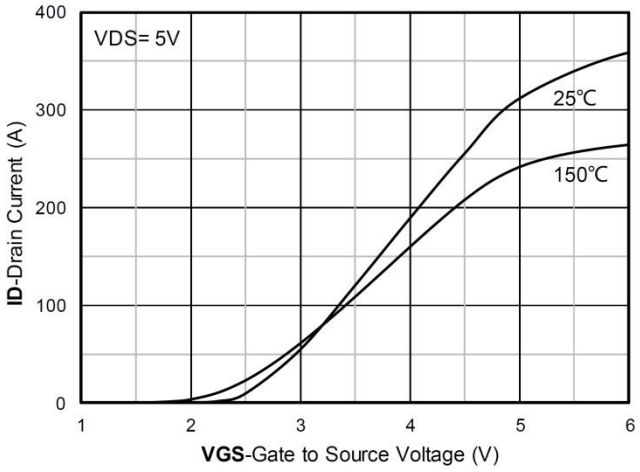
Note：

1. The EAS test condition is VDD=50V,VGS=10V,L=0.5mH,RG=25Ω

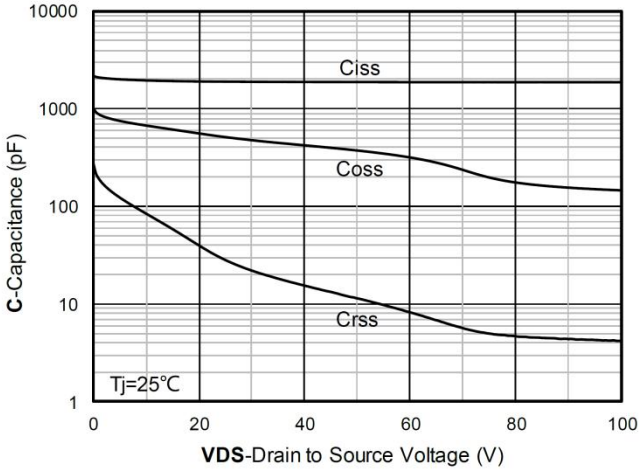
Typical Characteristics



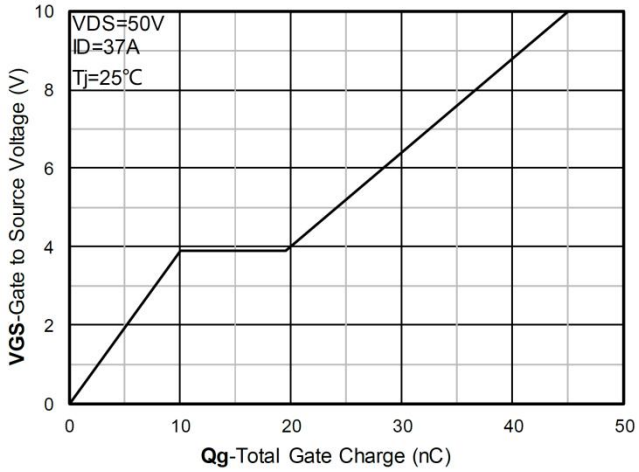
Output Characteristics



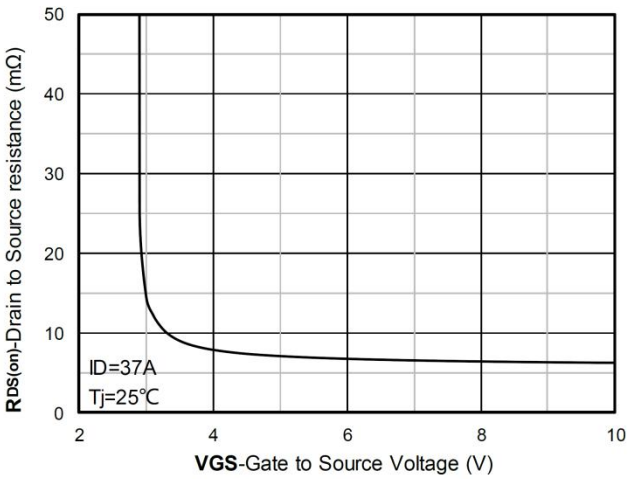
Transfer Characteristics



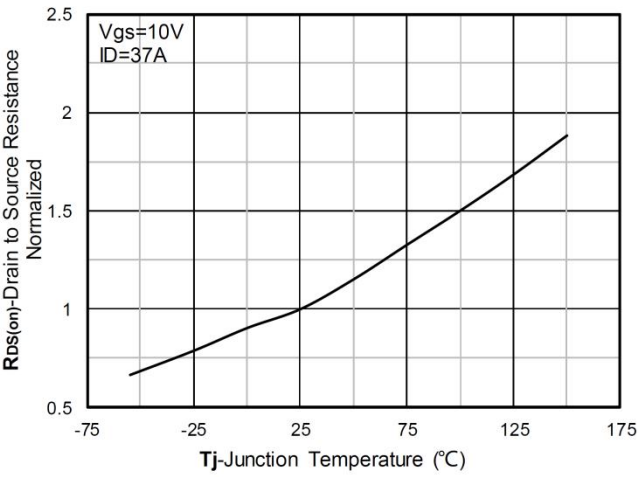
Capacitance Characteristics



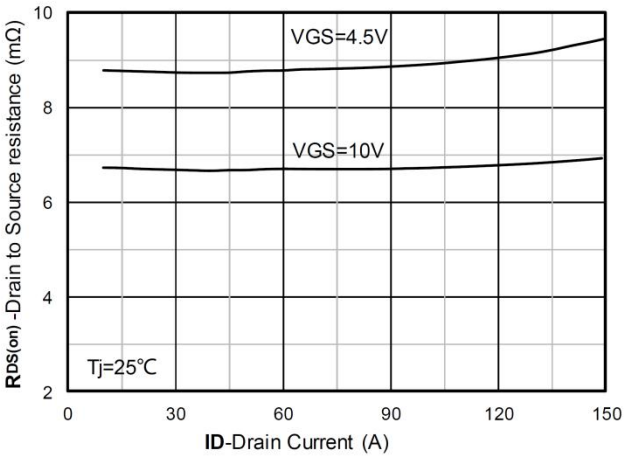
Gate Charge



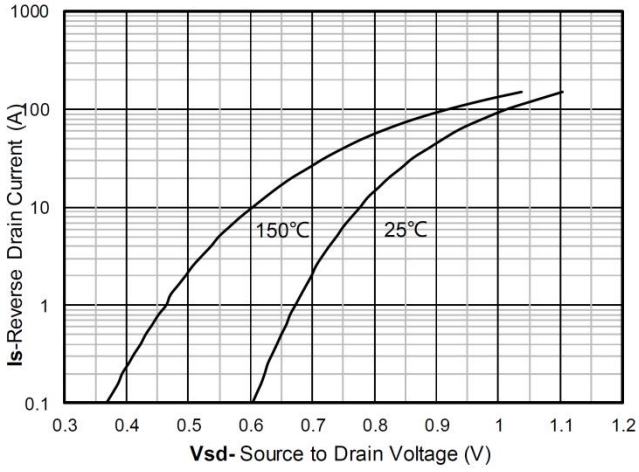
On-Resistance vs Gate to Source Voltage



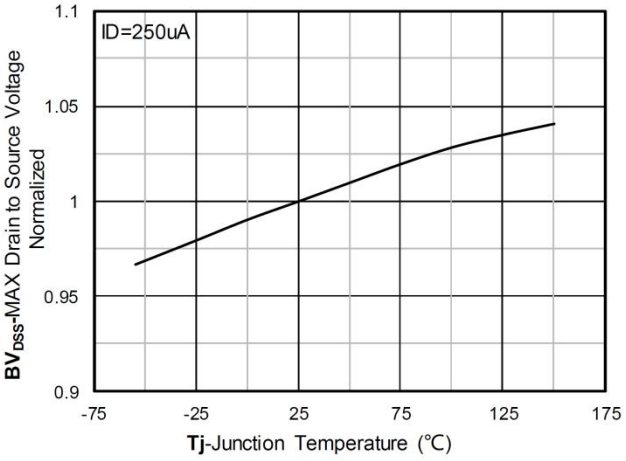
Normalized On-Resistance



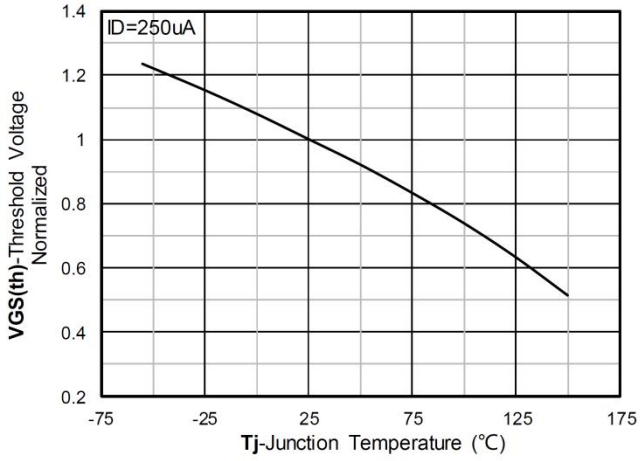
RDS(on) VS Drain Current



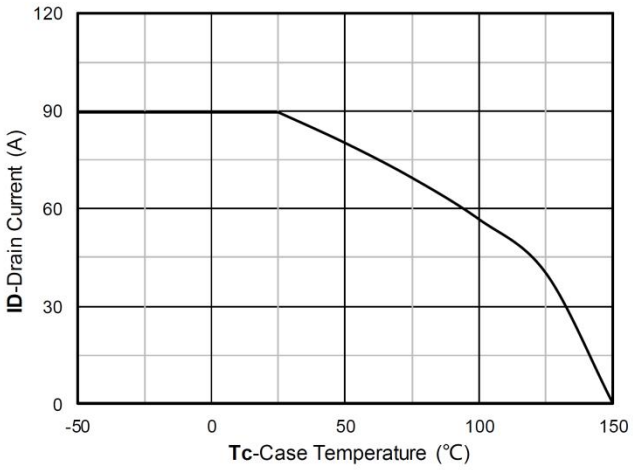
Forward characteristics of reverse diode



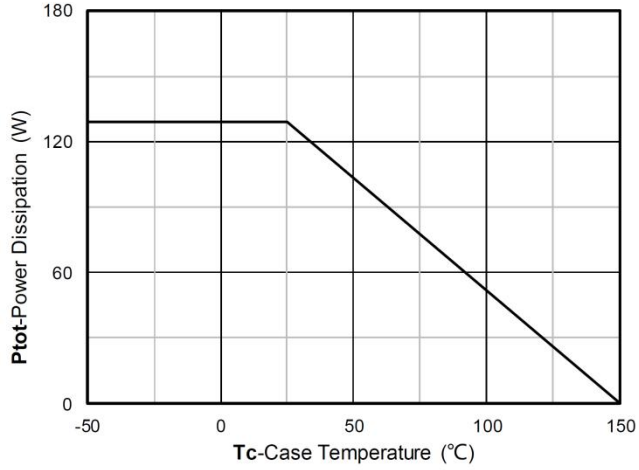
Normalized breakdown voltage



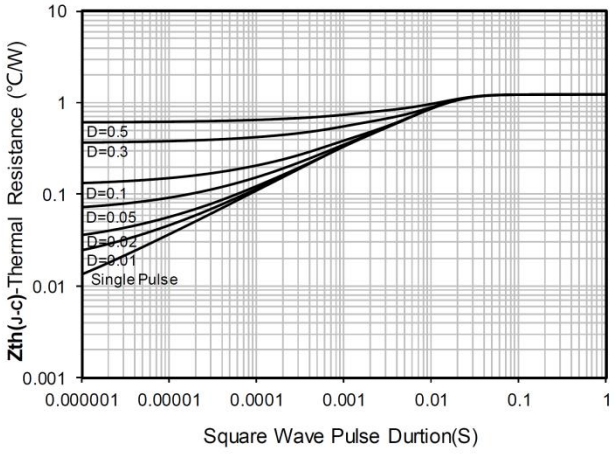
Normalized Threshold voltage



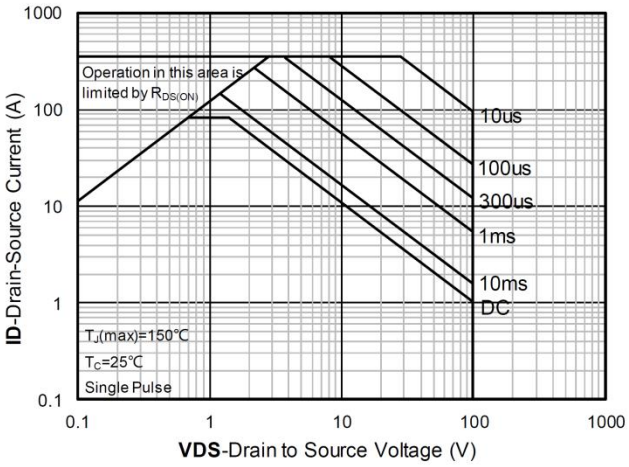
Current dissipation



Power dissipation

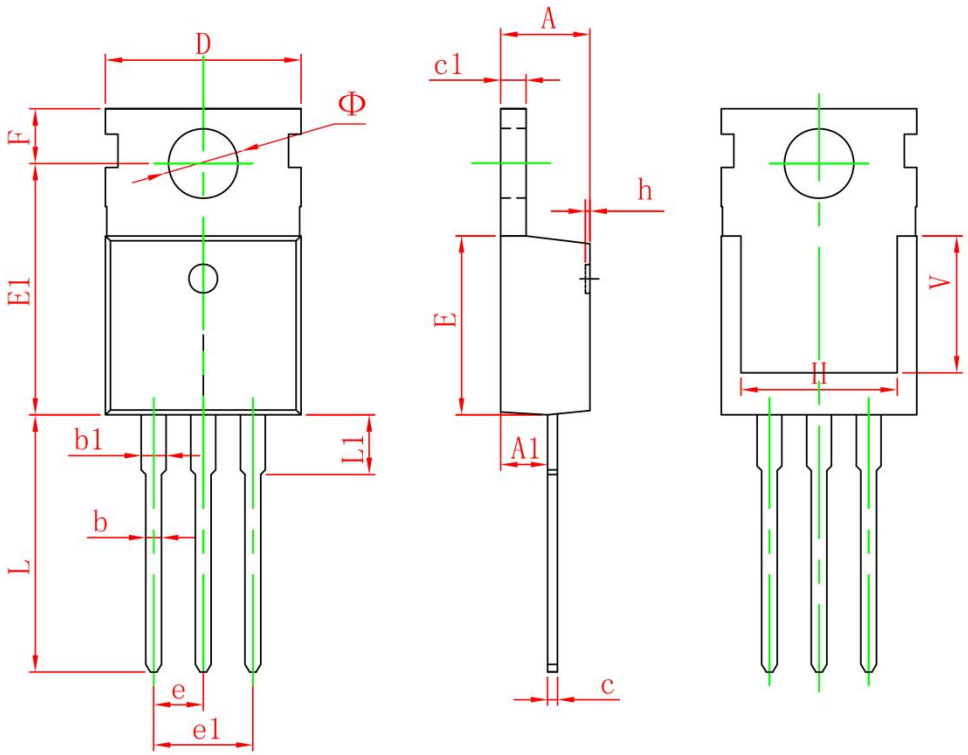


Maximum Transient Thermal Impedance



Safe Operation Area

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150